

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT404 (D2PAK) surface mountable plastic package intended for use in applications requiring very high inrush current capability, high thermal cycling performance and high junction temperature capability ($T_{j(max)}$ = 150 °C).

2. Features and benefits

- High bidirectional blocking voltage capability
- High junction operating temperature capability
- High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability
- Surface mountable package
- Very high current surge capability

3. Applications

- Capacitive Discharge Ignition (CDI)
- Crowbar protection
- Inrush protection
- Motor control
- Voltage regulation

4. Quick reference data

| Table 1. Quick reference data | | | | | | | |
|-------------------------------|--|--|--|-----|-----|-----|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| V _{DRM} | repetitive peak off- state voltage | | | - | - | 600 | V |
| V _{RRM} | repetitive peak reverse voltage | | | - | - | 600 | V |
| I _{TSM} | non-repetitive peak on- state current | half sine wave; T _{j(init)} = 25 °C; t _p = 10 ms; <u>Fig. 4</u> ; <u>Fig. 5</u> | | - | - | 210 | A |
| | | half sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 8.3 \text{ ms}$ | | - | - | 231 | A |
| Tj | junction temperature | | | - | - | 150 | °C |





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| Symbol | Parameter | Conditions | Min | Тур | Мах | Unit |
|---------------------|-----------------------------------|--|-----|-----|-----|------|
| I _{T(RMS)} | RMS on-state current | half sine wave; T _{mb} ≤ 129 °C; <u>Fig. 2;</u> <u>Fig. 3</u> | - | - | 20 | А |
| Static chara | acteristics | | | | | |
| I _{GT} | gate trigger current | V_D = 12 V; I _T = 0.1 A; T _j = 25 °C; <u>Fig. 7</u> | - | 4.5 | 32 | mA |
| Dynamic ch | naracteristics | · · · · · · · · · · · · · · · · · · · | | | | |
| dV _D /dt | rate of rise of off-state voltage | V_{DM} = 402 V; T _j = 150 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit | 300 | - | - | V/µs |

5. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|-----------------------------------|--------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | к | cathode | mb | A H K |
| 2 | А | anode | | G sym037 |
| 3 | G | gate | | |
| mb | A | mounting base; connected to anode | | |
| | | | D2PAK (SOT404) | |

6. Ordering information

| Table 3. Ordering inf | formation | | |
|-----------------------|-----------|--|---------|
| Type number | Package | | |
| | Name | Description | Version |
| TYN20B-600T | D2PAK | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404 |

7. Marking

| Table 4. Marking codes | |
|------------------------|--------------|
| Type number | Marking code |
| TYN20B-600T | TYN20B-600T |

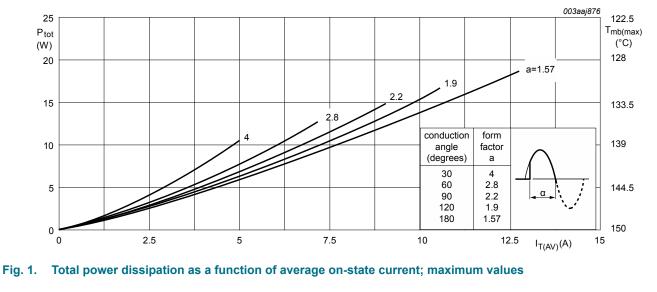
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8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---------------------|--------------------------------------|---|-----|-------|------------------|
| V _{DRM} | repetitive peak off-state voltage | | - | 600 | V |
| V _{RRM} | repetitive peak reverse voltage | | - | 600 | V |
| I _{T(AV)} | average on-state current | half sine wave; $T_{mb} \le 129 \text{ °C}$; Fig. 1 | - | 12.7 | А |
| I _{T(RMS)} | RMS on-state current | half sine wave; $T_{mb} \le 129 \text{ °C}$; Fig. 2; Fig. 3 | - | 20 | A |
| I _{TSM} | non-repetitive peak on-state current | half sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 10 \text{ ms}; Fig. 4; Fig. 5$ | - | 210 | A |
| | | half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 8.3 \text{ ms}$ | - | 231 | A |
| l ² t | I ² t for fusing | t _p = 10 ms; sine-wave pulse | - | 220.5 | A ² s |
| dl _T /dt | rate of rise of on-state current | I _T = 40 A; I _G = 200 mA; dI _G / dt = 200 mA/µs | - | 50 | A/µs |
| I _{GM} | peak gate current | | - | 5 | А |
| V _{RGM} | peak reverse gate voltage | | - | 5 | V |
| P _{GM} | peak gate power | | - | 20 | W |
| P _{G(AV)} | average gate power | over any 20 ms period | - | 1 | W |
| T _{stg} | storage temperature | | -40 | 150 | °C |
| Tj | junction temperature | | - | 150 | °C |

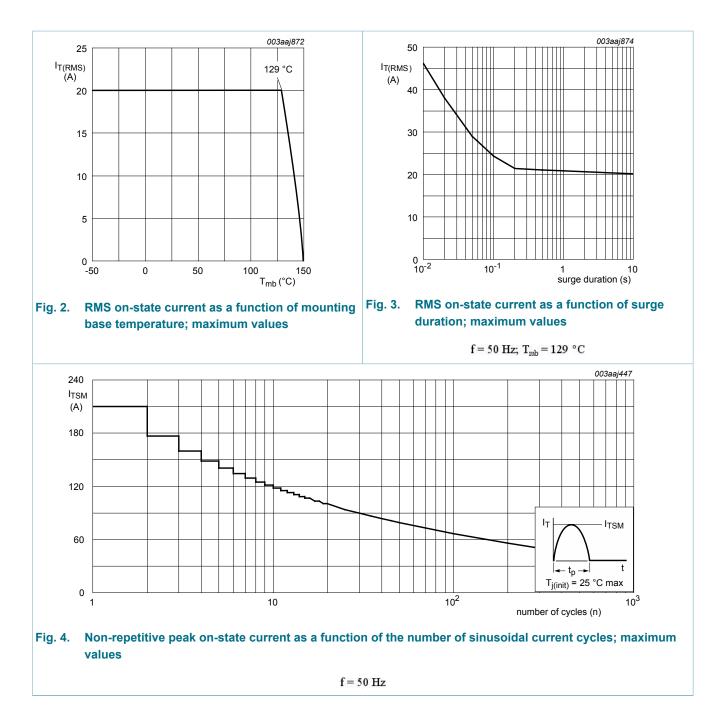


 $\mathbf{a} = \mathbf{form} \,\, \mathbf{factor} = \mathbf{I}_{T(RMS)} \, / \,\, \mathbf{I}_{T(AV)}$

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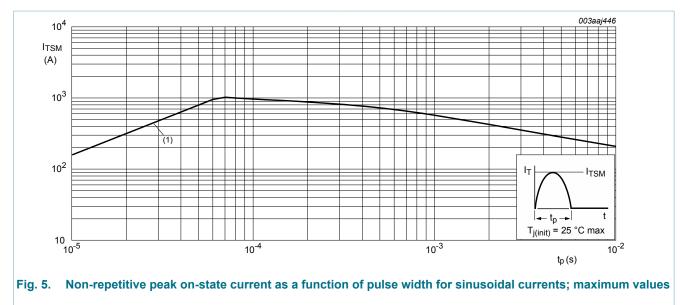
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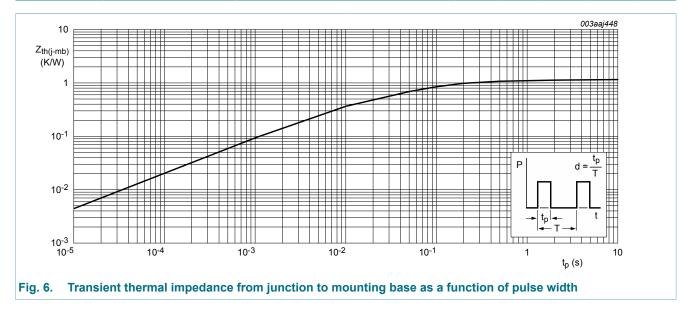
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 $t_p \leq 10 ms;$ (1) $dI_T / dt limit$

9. Thermal characteristics

| Table 6. Thermal characteristics | | | | | | | |
|----------------------------------|---|------------------------------|--|-----|-----|-----|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| R _{th(j-mb)} | thermal resistance from junction to mounting base | <u>Fig. 6</u> | | - | - | 1.1 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | minimum footprint, FR4 board | | - | 55 | - | K/W |



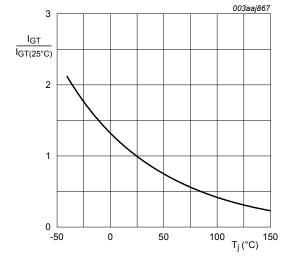
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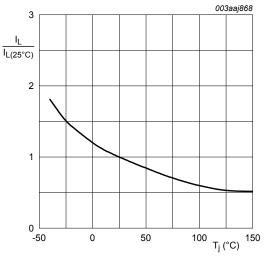
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10. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|-----------------------------------|--|-----|-----|-----|------|
| Static chara | acteristics | | | | | |
| I _{GT} | gate trigger current | V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; <u>Fig. 7</u> | - | 4.5 | 32 | mA |
| IL | latching current | V_D = 12 V; I _G = 0.1 A; T _j = 25 °C; Fig. 8 | - | 21 | 60 | mA |
| I _H | holding current | V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u> | - | 16 | 40 | mA |
| V _T | on-state voltage | I _T = 32 A; T _j = 25 °C; <u>Fig. 10</u> | - | 1.2 | 1.5 | V |
| V _{GT} | gate trigger voltage | V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11 | - | 0.7 | 1.3 | V |
| | | V _D = 400 V; I _T = 0.1 A; T _j = 150 °C; Fig. 11 | 0.2 | 0.4 | - | V |
| I _D | off-state current | V _D = 600 V; T _j = 150 °C | - | 0.2 | 1 | mA |
| I _R | reverse current | V _R = 600 V; T _j = 150 °C | - | 0.2 | 1 | mA |
| Dynamic cl | haracteristics | | 1 | - 1 | | |
| dV _D /dt | rate of rise of off-state voltage | V_{DM} = 402 V; T _j = 150 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit | 300 | - | - | V/µs |



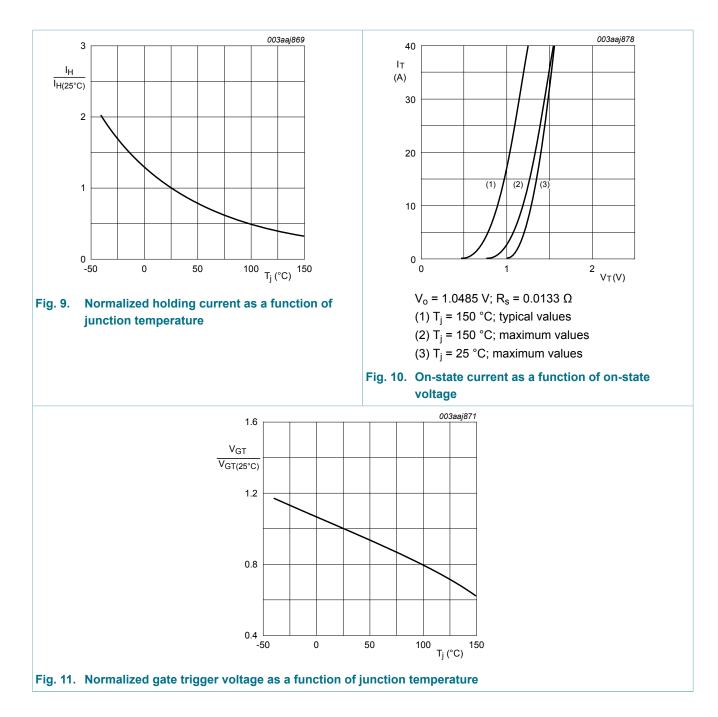




8. Normalized latching current as a function of junction temperature

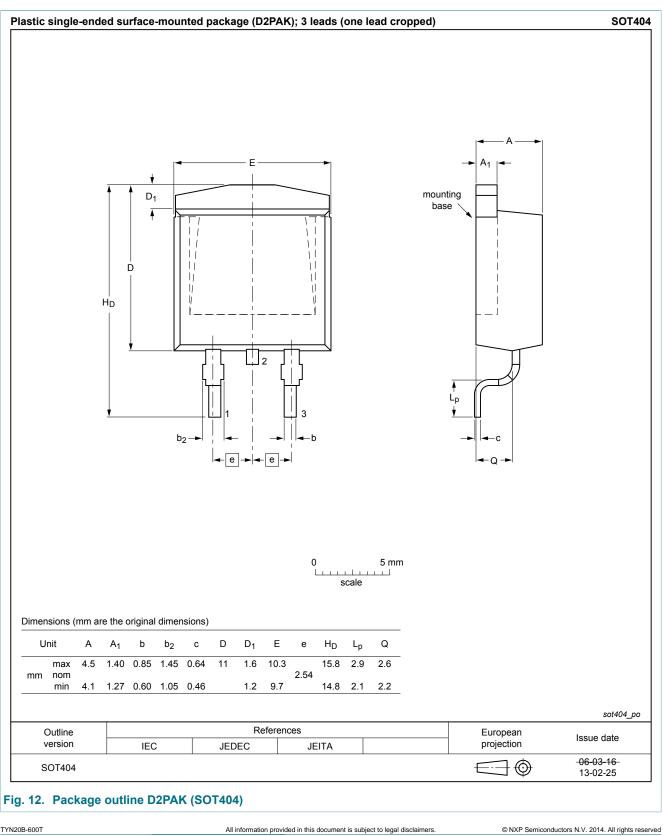
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11. Package outline



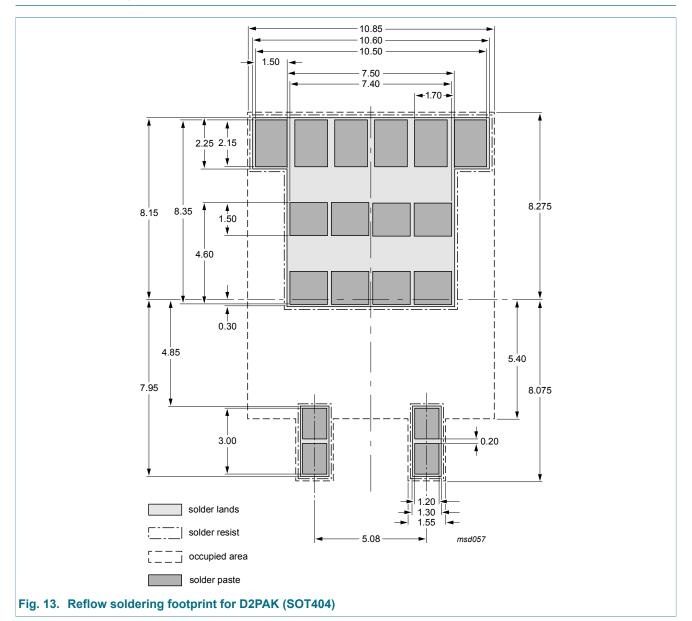
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12. Soldering



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13. Legal information

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|--------------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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